



## General Description

AFC3346W, N & P Pair enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

## Features

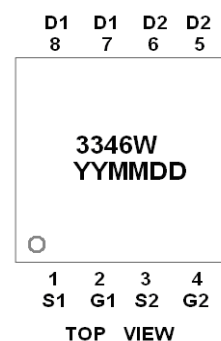
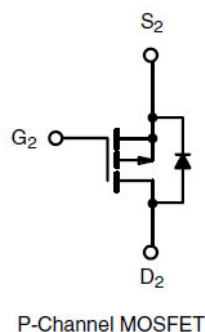
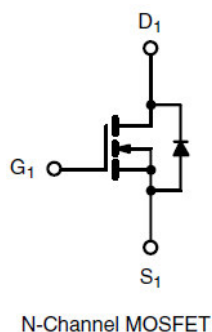
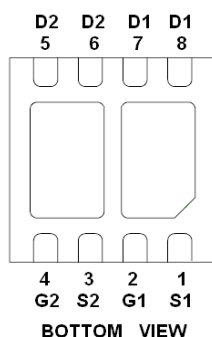
N-Channel

- 40V/15A,  $R_{DS(ON)} = 28m\Omega @ V_{GS} = 10V$
- 40V/12A,  $R_{DS(ON)} = 38m\Omega @ V_{GS} = 4.5V$

P-Channel

- -40V/-12A,  $R_{DS(ON)} = 45m\Omega @ V_{GS} = -10V$
- -40V/-10A,  $R_{DS(ON)} = 62m\Omega @ V_{GS} = -4.5V$

## Pin Description ( DFN3X3-8L )



## Application

- DC/DC Conversion
- Load Switch
- DC FAN

## Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFC3346WFN338RG	3346W YYMMDD	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code

※ MM month code

※ DD date code

※ AFC3346WFN338RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



### Absolute Maximum Ratings ( N-Channel )

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	15
		T <sub>A</sub> =70°C	12
Pulsed Drain Current	I <sub>DM</sub>	40	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	10	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2
		T <sub>A</sub> =70°C	1.5
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	56	°C/W

### Electrical Characteristics ( N-Channel )

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0		3.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =10V	20			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A		20	28	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A		30	38	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =5.0A		25		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V I <sub>D</sub> = 5A		10	14	nC
Gate-Source Charge	Q <sub>gs</sub>			2.8		
Gate-Drain Charge	Q <sub>gd</sub>			3.2		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V f=1MHz		850		pF
Output Capacitance	C <sub>oss</sub>			110		
Reverse Transfer Capacitance	C <sub>rss</sub>			75		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, R <sub>L</sub> =4Ω I <sub>D</sub> ≅5.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =1Ω		6	12	ns
	t <sub>r</sub>			10	20	
Turn-Off Time	t <sub>d(off)</sub>			20	36	
	t <sub>f</sub>			6	12	



**Absolute Maximum Ratings ( P-Channel )**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-40	V
Gate -Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-12.0
		T <sub>A</sub> =70°C	-10.0
Pulsed Drain Current	I <sub>DM</sub>	-40	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-10	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	1.8
		T <sub>A</sub> =70°C	1.2
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	62.5	°C/W

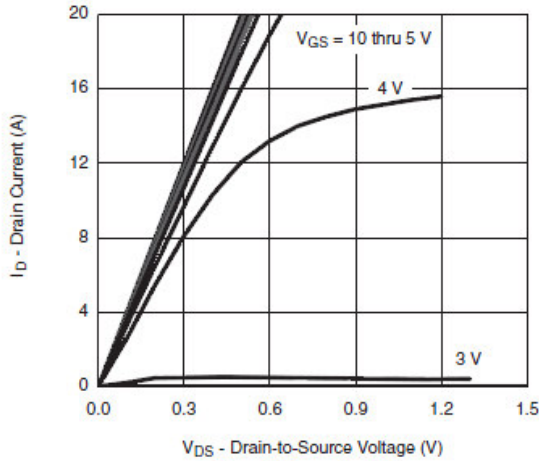
**Electrical Characteristics ( P-Channel )**

(T<sub>A</sub>=25°C Unless otherwise noted)

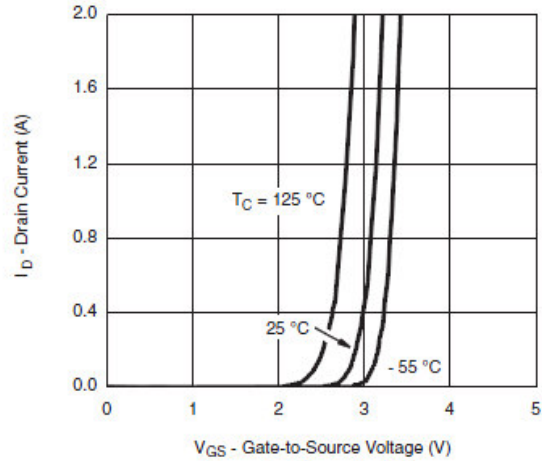
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = -250uA	-40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1.0		-3.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -32V, V <sub>GS</sub> =0V			-1	
		V <sub>DS</sub> = -32V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-20	uA
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -5V, V <sub>GS</sub> = -10V	-20			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> =-12A		34	45	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-10A		48	62	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -5A		20		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -2A, V <sub>GS</sub> =0V		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V I <sub>D</sub> = -5.0A		13	20	nC
Gate-Source Charge	Q <sub>gs</sub>			4.5		
Gate-Drain Charge	Q <sub>gd</sub>			6.5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V f=1MHz		1100		pF
Output Capacitance	C <sub>oss</sub>			145		
Reverse Transfer Capacitance	C <sub>rss</sub>			115		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-20V, R <sub>L</sub> =4Ω I <sub>D</sub> ≡-5.0A, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =1Ω		40	80	ns
	t <sub>r</sub>			55	100	
Turn-Off Time	t <sub>d(off)</sub>			30	60	
	t <sub>f</sub>			12	20	



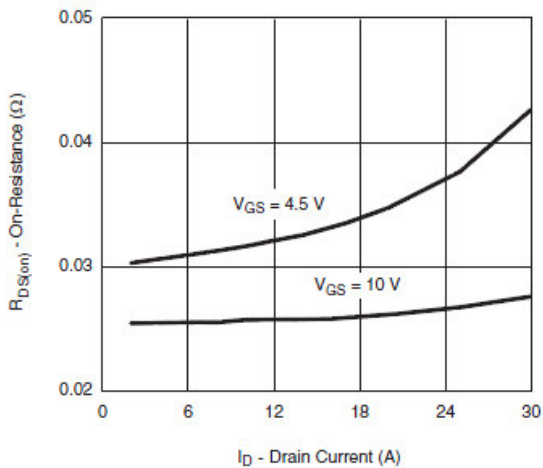
**Typical Characteristics ( N-Channel )**



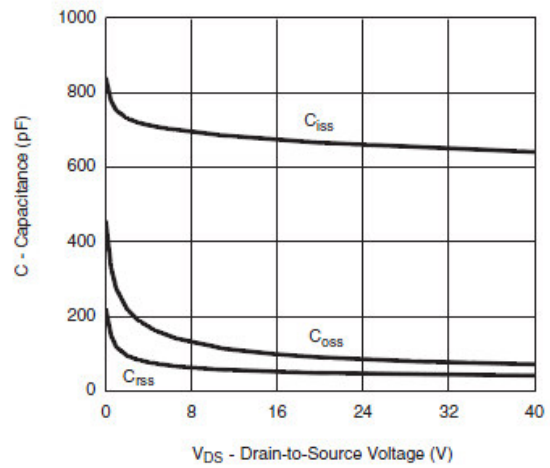
**Output Characteristics**



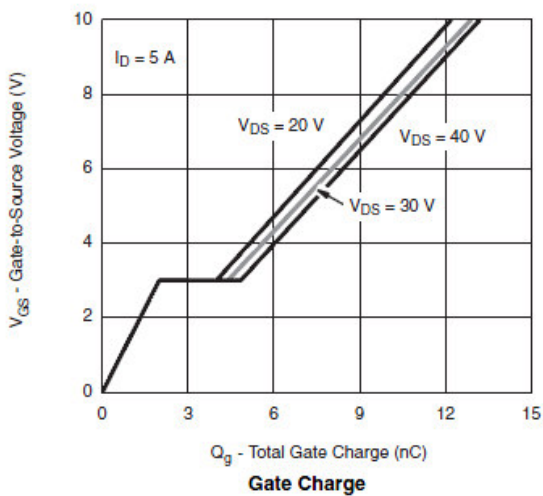
**Transfer Characteristics**



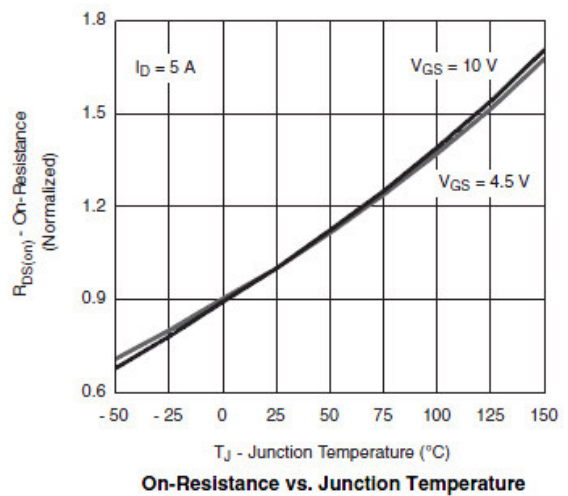
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



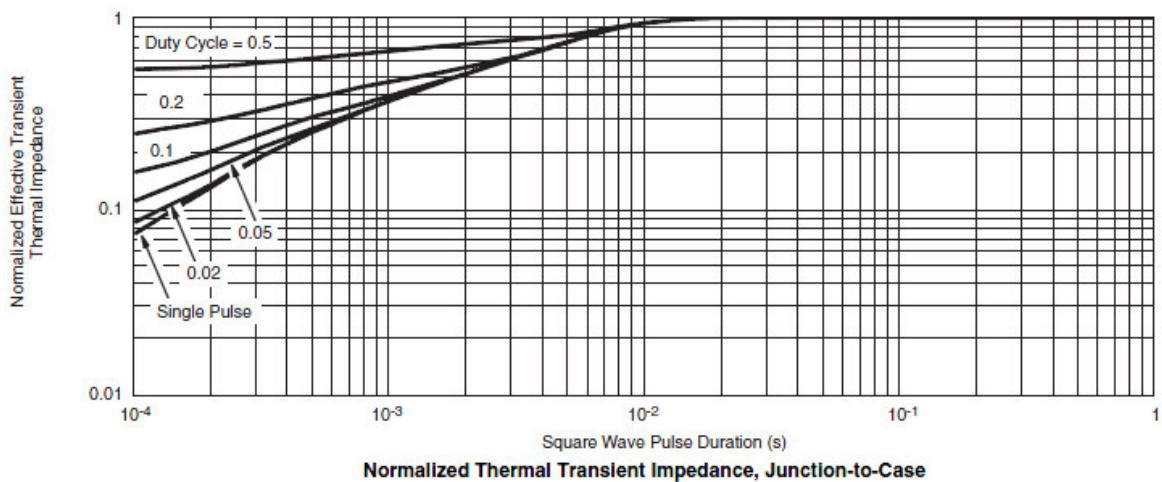
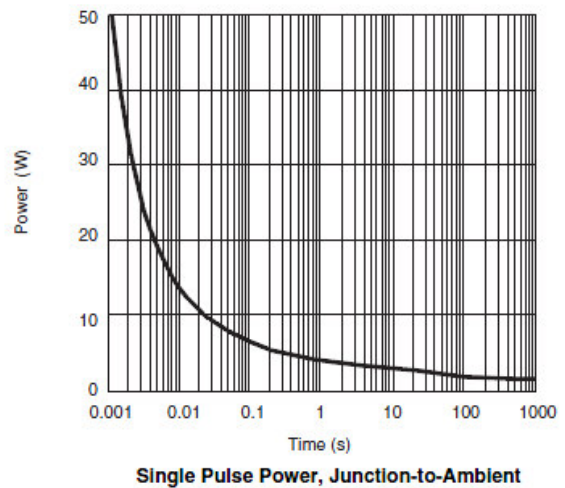
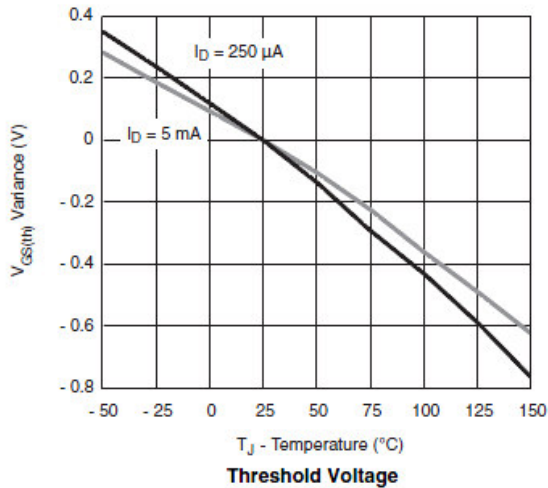
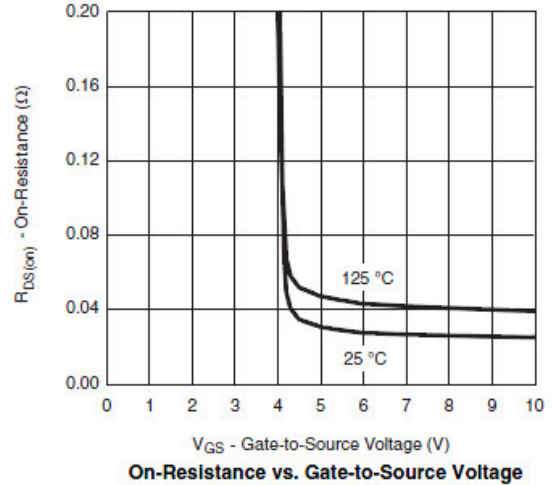
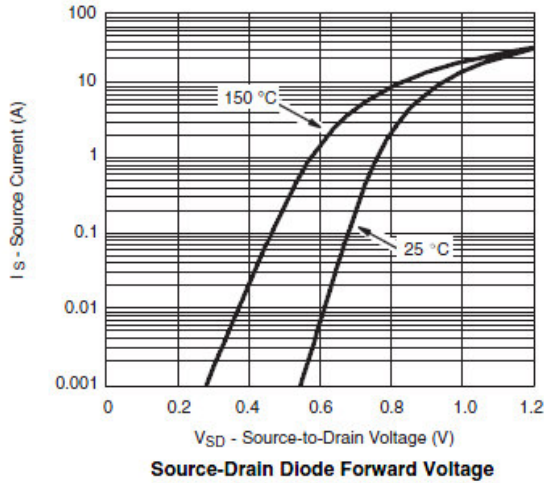
**Gate Charge**



**On-Resistance vs. Junction Temperature**

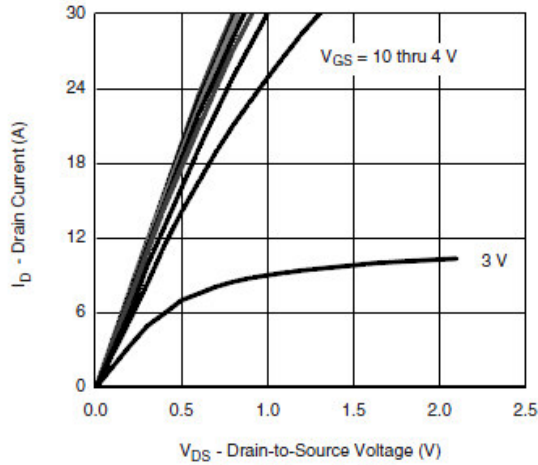


## Typical Characteristics ( N-Channel )

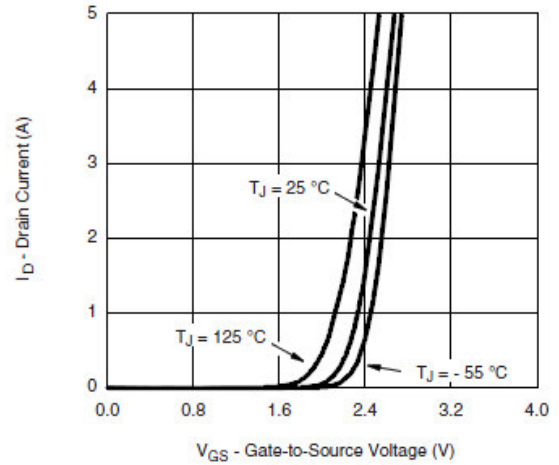




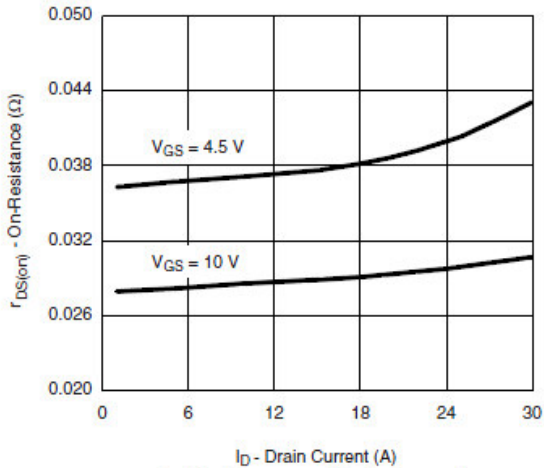
**Typical Characteristics ( P-Channel )**



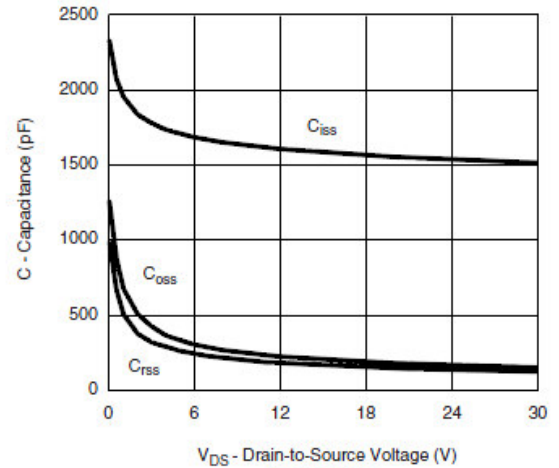
**Output Characteristics**



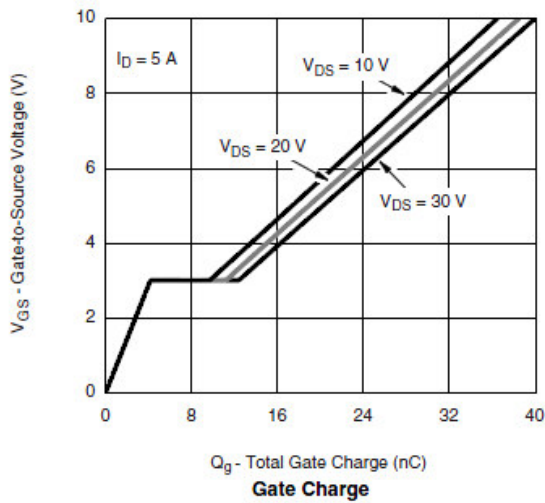
**Transfer Characteristics**



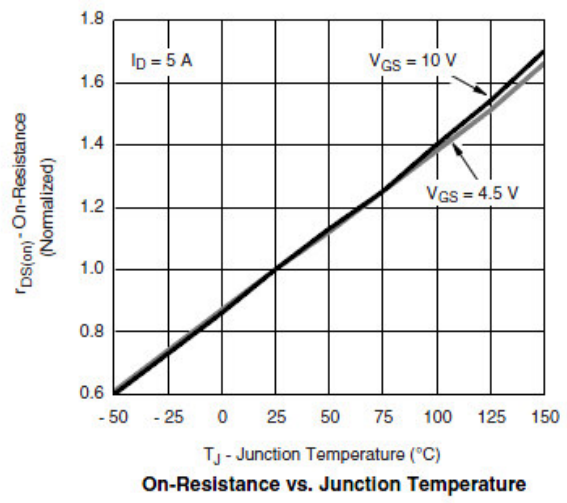
**On-Resistance vs. Drain Current**



**Capacitance**



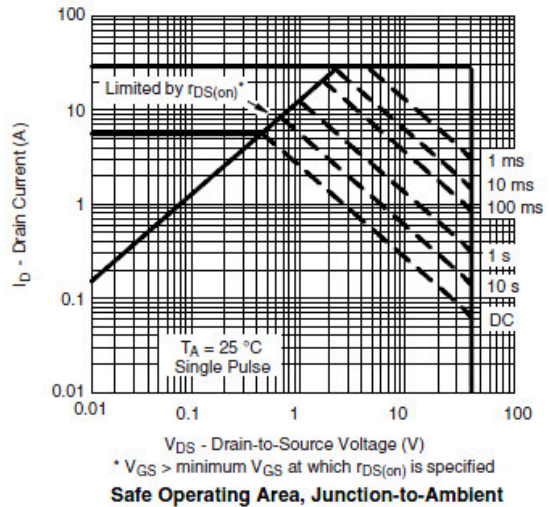
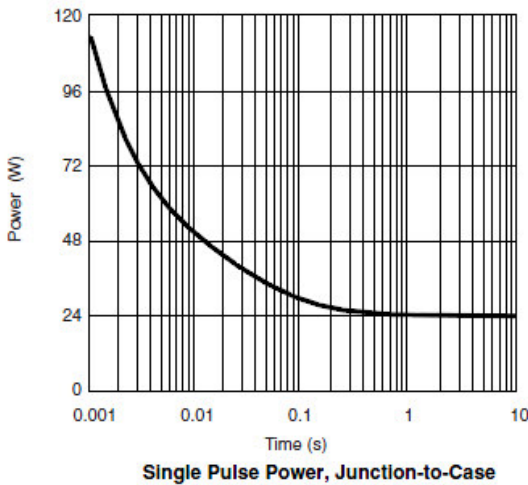
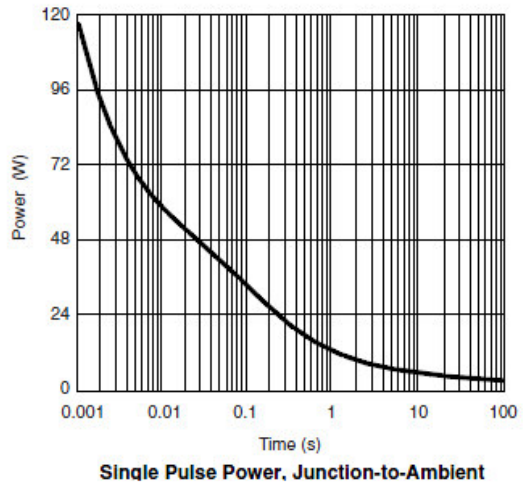
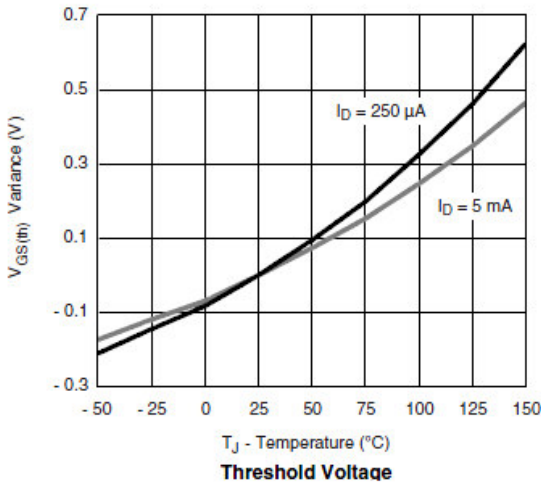
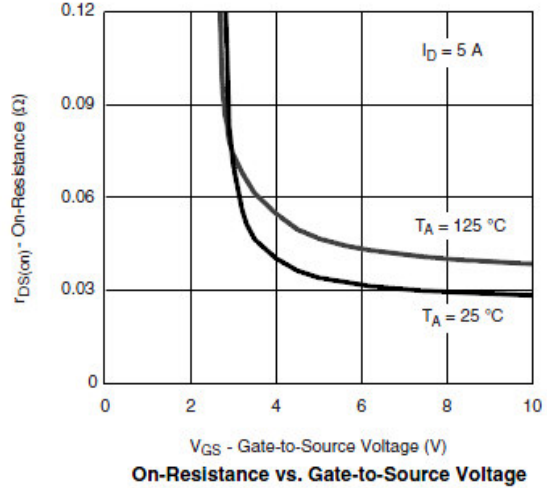
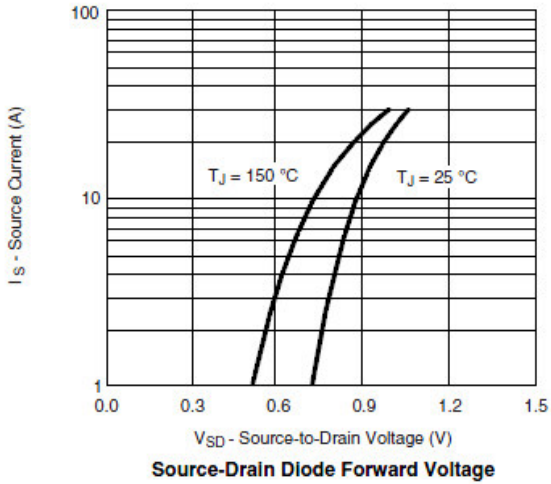
**Gate Charge**



**On-Resistance vs. Junction Temperature**



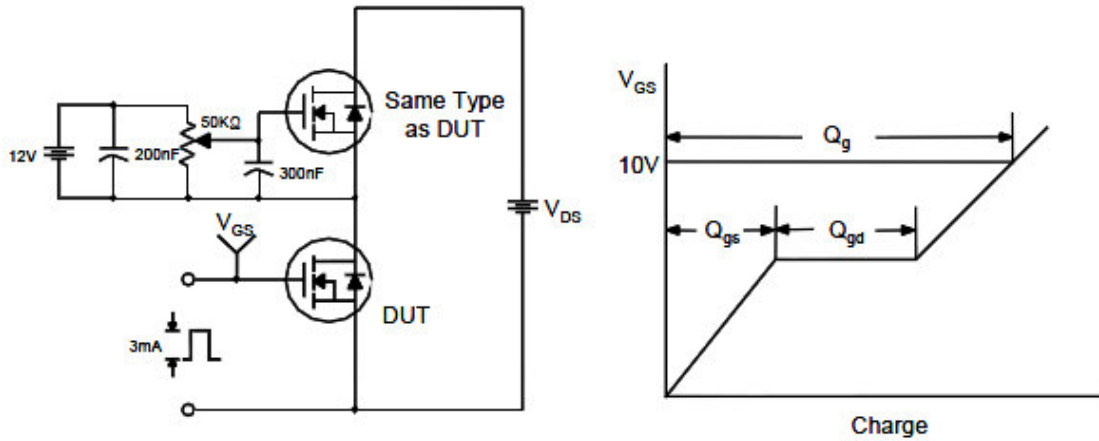
## Typical Characteristics ( P-Channel )



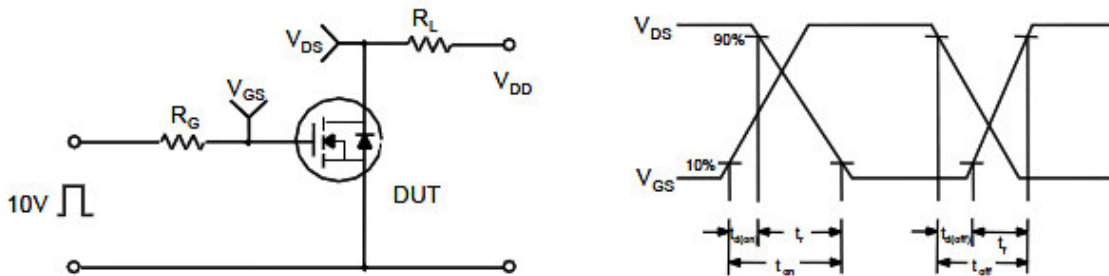


**Typical Characteristics**

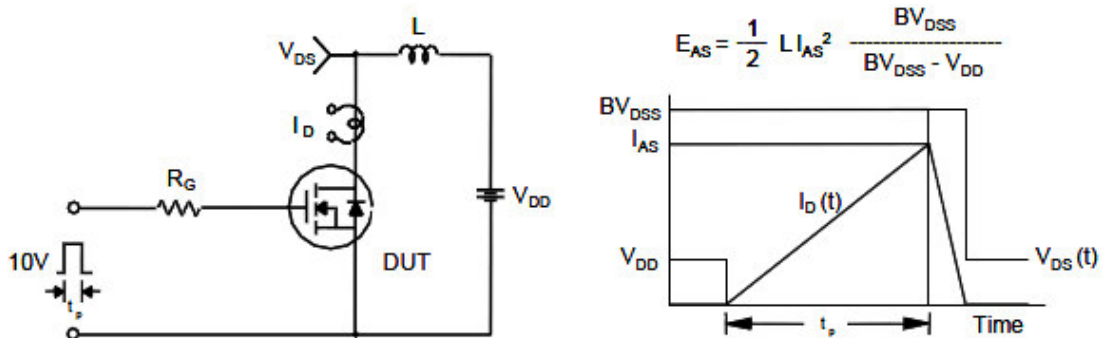
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



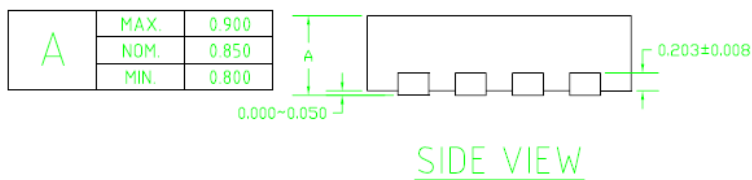
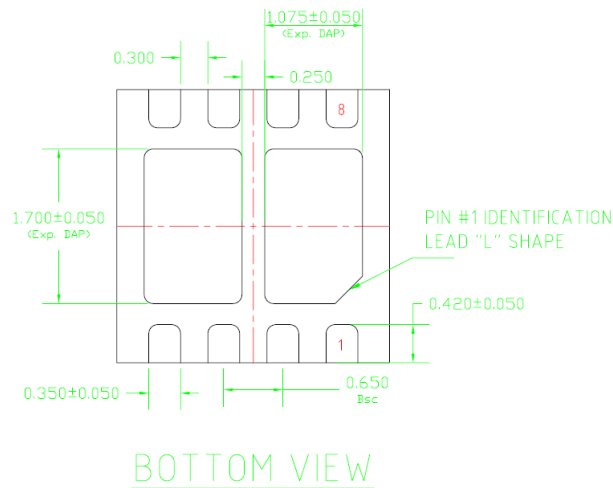
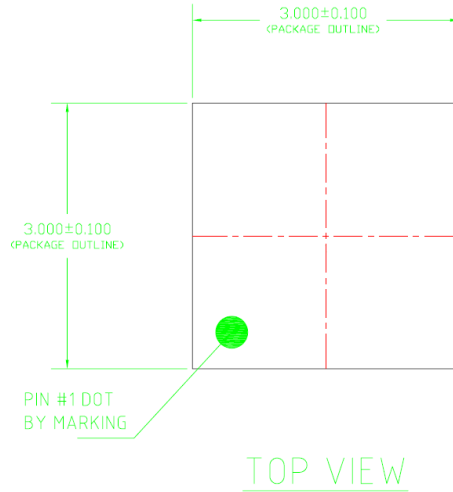
Unclamped Inductive Switching Test Circuit & Waveforms







**Package Information ( DFN3X3-8L )**



©2010 Alfa-MOS Technology Corp.  
 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)  
 Tel : 886 2) 2651 3928  
 Fax : 886 2) 2786 8483  
 ©http://www.alfa-mos.com